

NANO CHEM[®]

ASX-II™ Purification Medium NANO CHEM[®] Arsine Gas Purifier For Compound Semiconductor Epitaxy

Overview

The increasing demands for higher yields and more consistent performance in the fabrication of compound semiconductor devices dictate the need for more stringent contamination control. Nowhere is this more evident than in compound semiconductor epitaxy processes. Gas contaminants, especially moisture and oxygen-containing species, adversely affect film quality and reduce yields. Since contamination sources cannot be entirely eliminated, the most effective solution is to purify arsine as close to the point-of-use as possible with an effective and efficient purification medium.

ASX-II™ is an inorganic purification medium that removes H₂O and is expected to remove Oxy-acid impurities. ASX-II™ offers the highest lifetimes for the removal of moisture. ASX-II™ has a wide range of applications, including GaAs and InGaAsP MOCVD processes, and is available in a wide range of purifier sizes: from Point-of-Use to Proximate.

Features and Benefits

- Direct purification of AsH₃ used in ultra-high purity applications
- Ideal for GaAs and InGaAsP processes
- Highest moisture capacity
- No pressure build-up
- Best impurity removal efficiencies
- Removes: H₂O and is expected to remove other oxygenated species
- Minimizes fluctuations in volatile impurities as cylinder is depleted
- Minimizes cylinder-to-cylinder impurity variations
- Improves process yields and device quality
- Increased savings by using cylinder longer before change out
- No external power source required
- No heating or cooling required

Specifications

- < 75 ppb H₂O (LDL) in AsH₃ by MAH-2

Typical Performance

Impurities are typically removed to the detection limits of state-of-the-art analytical techniques:

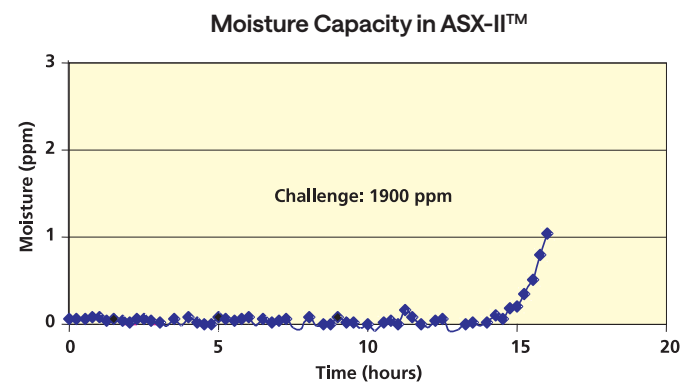
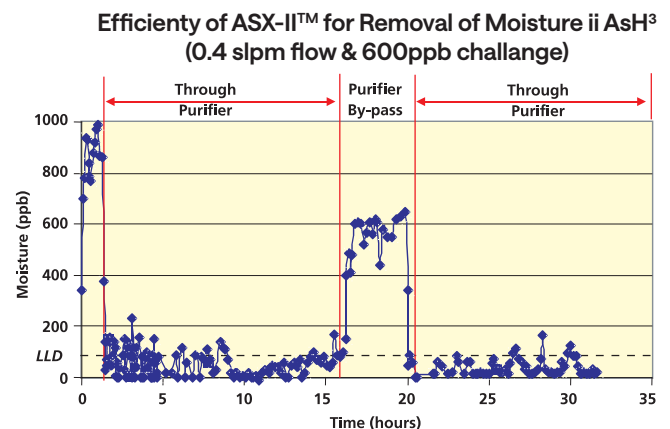
Impurity/Matrix	Efficiency (ppb)	Challenge (ppm)
H ₂ O in N ₂	< 100 (LDL)	1,900
H ₂ O in AsH ₃	< 75 (LDL)	660

Capacity & Efficiency in AsH₃

ASX-II™ offers the highest lifetime and the best efficiency for the removal of moisture in arsine.

Reduced Cost of Operation

By increasing the amount of arsine that can be consumed in each cylinder before a changeout, ASX-II™ enables significant raw material savings.



Purifier Models / Sizes

NANOCHEM® ASX-II™ purification medium is available in a wide variety of hardware configurations for point-of-use, distribution and source purification applications:

Model	Maximum Flow Rates in AsH ₃ Service		Maximum Allowable Media Volume	Working Pressure	
	slpm	(NM ₃ /hr)		psig	(Mpa)
L-Series*	8-150	(0.5-9)	60, 300 ml	60	(0.43)
A-Series*	50	(3)	60, 300, 500 ml	60	(0.43)

*The most common hardware designs used are the L-60, L-300 and the A-300l.

Options

Standard: 0.003 µm Teflon® particle filter with 99.9999999% retention for arsine service.

End-Point Detection is not available.

Equipment Technology Center

166 Keystone Drive
Montgomeryville, PA 18936
Tel: 800-828-4313 • Fax: 215-619-0458
Email: mathesonsales@us.nipponanso.com

Specifications are subject to change. Please check www.us.nipponanso.com for most current information.

NANOCHEM is a registered trademark of Nippon Sanso Matheson, Inc.

ASX-II and PHX are trademarks of Nippon Sanso Matheson, Inc.

VCR is a trademark of Swagelok Co. Telfon is a registered trademark of E.I. du Pont de Nemours & Co.

Printed in USA PB040 R09/2026

